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PATENT ABSTRACTS OF JAPAN

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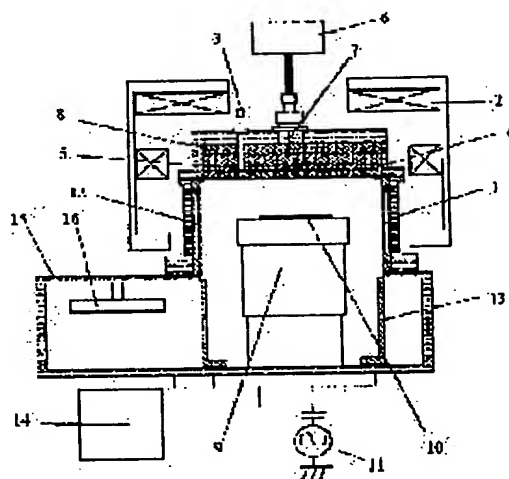
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(54) PLASMA PROCESSING DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To efficiently form high density plasma necessary for etching an oxide film, from the viewpoint of energy saving and costs reduction.

SOLUTION: Microwave of a UHF band are emitted from the periphery of a disc-like plate antenna 5 to generate plasma due to electronic cyclotron resonance, and also the plate thickness of a gas supply plate 4 provided on a face at the plasma side of the antenna 5 is increased by more than the skin depth of the microwave. Since an oxide film is etched by the use of low electronic temperature high-density plasma, etching results of superior characteristics are obtained, and energy-saving and cost-reducing device can be obtained.



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